

# BLM7G1822S-40PB; BLM7G1822S-40PBG

LDMOS 2-stage power MMIC

Rev. 2 — 24 March 2014

Product data sheet

## 1. Product profile

### 1.1 General description

The BLM7G1822S-40PB(G) is a dual section, 2-stage power MMIC using NXP's state of the art GEN7 LDMOS technology. This multiband device is perfectly suited as general purpose driver or small cell final in the frequency range from 1805 MHz to 2170 MHz. Available in gull wing or straight lead outline.

**Table 1. Application performance**

Typical RF performance at  $T_{case} = 25\text{ °C}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 120\text{ mA}$ .

Test signal: 3GPP test model 1; 64 DPCH; PAR = 10 dB at 0.01% probability on CCDF; per section unless otherwise specified in a class-AB production circuit.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	η <sub>D</sub>	ACPR <sub>5M</sub>
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
single carrier W-CDMA	2167.5	28	4	31.5	25	-38.5

### 1.2 Features and benefits

- Designed for broadband operation (frequency 1805 MHz to 2170 MHz)
- High section-to-section isolation enabling multiple combinations
- Integrated temperature compensated bias
- Biasing of individual stages is externally accessible
- Integrated ESD protection
- Excellent thermal stability
- High power gain
- On-chip matching for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

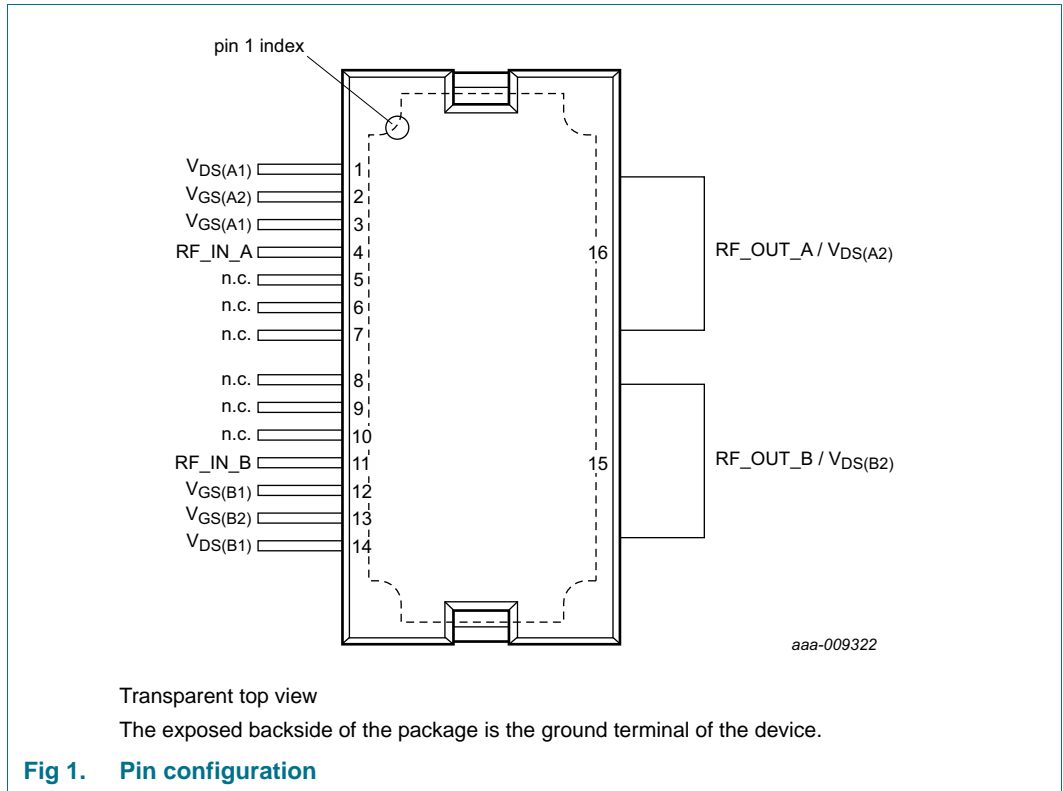
### 1.3 Applications

- RF power MMIC for W-CDMA base stations in the 1805 MHz to 2170 MHz frequency range. Possible circuit topologies are the following as also depicted in [Section 8.1](#):
  - ◆ Dual section or single ended
  - ◆ Doherty
  - ◆ Quadrature combined
  - ◆ Push-pull



## 2. Pinning information

### 2.1 Pinning



### 2.2 Pin description

**Table 2. Pin description**

Symbol	Pin	Description
$V_{DS(A1)}$	1	drain-source voltage of stage A1
$V_{GS(A2)}$	2	gate-source voltage of stage A2
$V_{GS(A1)}$	3	gate-source voltage of stage A1
RF_IN_A	4	RF input section A
n.c.	5	not connected
n.c.	6	not connected
n.c.	7	not connected
n.c.	8	not connected
n.c.	9	not connected
n.c.	10	not connected
RF_IN_B	11	RF input section B
$V_{GS(B1)}$	12	gate-source voltage of stage B1
$V_{GS(B2)}$	13	gate-source voltage of stage B2
$V_{DS(B1)}$	14	drain-source voltage of stage B1

**Table 2. Pin description ...continued**

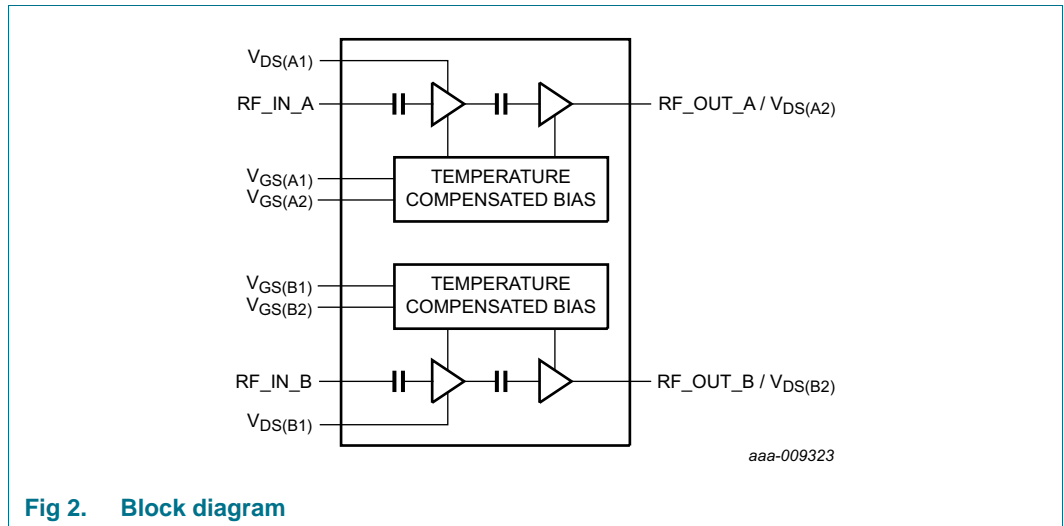
Symbol	Pin	Description
RF_OUT_B/ $V_{DS(B2)}$	15	RF output section B / drain-source voltage of stage B2
RF_OUT_A/ $V_{DS(A2)}$	16	RF output section A / drain-source voltage of stage A2
GND	flange	RF ground

### 3. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BLM7G1822S-40PB	HSOP16F	plastic, heatsink small outline package; 16 leads (flat)	SOT1211-1
BLM7G1822S-40PBG	HSOP16	plastic, heatsink small outline package; 16 leads	SOT1212-1

### 4. Block diagram



**Fig 2. Block diagram**

### 5. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature	[1]	-	225	°C
$T_{case}$	case temperature		-	150	°C

[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

## 6. Thermal characteristics

**Table 5. Thermal characteristics**

Measured for total device.

Symbol	Parameter	Conditions	Value	Unit	
R <sub>th(j-c)</sub>	thermal resistance from junction to case	final stage; T <sub>case</sub> = 90 °C; P <sub>L</sub> = 2.52 W	[1]	1.2	K/W
		driver stage; T <sub>case</sub> = 90 °C; P <sub>L</sub> = 2.52 W	[1]	3.8	K/W

[1] When operated with a CW signal.

## 7. Characteristics

**Table 6. DC characteristics**

T<sub>case</sub> = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Final stage</b>						
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 0.302 mA	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 30.2 mA	1.4	1.8	2.4	V
V <sub>GSq</sub>	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 120 mA	1.55	1.9	2.35	V
		V <sub>DS</sub> = 28 V; I <sub>D</sub> = 120 mA	[1]	1.9	2.3	2.9
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μA
I <sub>DSX</sub>	drain cut-off current	V <sub>GS</sub> = V <sub>GS(th)</sub> + 3.75 V; V <sub>DS</sub> = 10 V	-	5.4	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 1.0 V; V <sub>DS</sub> = 0 V	-	-	140	nA
<b>Driver stage</b>						
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 0.058 mA	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 5.8 mA	1.4	1.8	2.4	V
V <sub>GSq</sub>	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 40 mA	1.65	2	2.45	V
		V <sub>DS</sub> = 28 V; I <sub>D</sub> = 40 mA	[2]	1.9	2.4	2.9
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μA
I <sub>DSX</sub>	drain cut-off current	V <sub>GS</sub> = V <sub>GS(th)</sub> + 3.75 V; V <sub>DS</sub> = 10 V	-	1.04	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 1.0 V; V <sub>DS</sub> = 0 V	-	-	140	nA

[1] In production circuit with 825 Ω gate feed resistor.

[2] In production circuit with 850 Ω gate feed resistor.

**Table 7. RF Characteristics**

Typical RF performance at  $T_{case} = 25\text{ °C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 120\text{ mA}$ ;  $P_{L(AV)} = 4\text{ W}$ . Per section unless otherwise specified, measured in a NXP wideband  $f = 1807.5\text{ MHz}$  to  $2167.5\text{ MHz}$  production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Test signal: single carrier W-CDMA [1]</b>						
$G_p$	power gain	$f = 1807.5\text{ MHz}$	-	31	-	dB
		$f = 2167.5\text{ MHz}$	30	31.5	33	dB
$\eta_D$	drain efficiency	$f = 1807.5\text{ MHz}$	-	24.5	-	%
		$f = 2167.5\text{ MHz}$	22	25	-	%
$RL_{in}$	input return loss	$f = 2167.5\text{ MHz}$	-	-15	-10	dB
$ACPR_{5M}$	adjacent channel power ratio (5 MHz)	$f = 1807.5\text{ MHz}$	-	-40.5	-	dBc
		$f = 2167.5\text{ MHz}$	-	-38.5	-36.5	dBc
$PAR_O$	output peak-to-average ratio	$f = 1807.5\text{ MHz}$	-	8	-	dB
		$f = 2167.5\text{ MHz}$	7.2	7.7	-	dB
$\Delta I_{Dq}/\Delta T$	quiescent drain current variation with temperature	$T = -40\text{ °C}$ to $+85\text{ °C}$				
		final stage $I_{Dq}$ ; gate feed resistor = $825\ \Omega$	-	$\pm 1$	-	%
		driver stage $I_{Dq}$ ; gate feed resistor = $850\ \Omega$	-	$\pm 1$	-	%
<b>Test signal: CW [2]</b>						
$\Delta\phi_{s21}$	phase response difference	between sections	-10	-	+10	deg
$\Delta S_{21} ^2$	insertion power gain difference	between sections	-0.5	-	+0.5	dB

[1] 3GPP test model 1; 64 DPCH; PAR = 10 dB at 0.01% probability on CCDF.

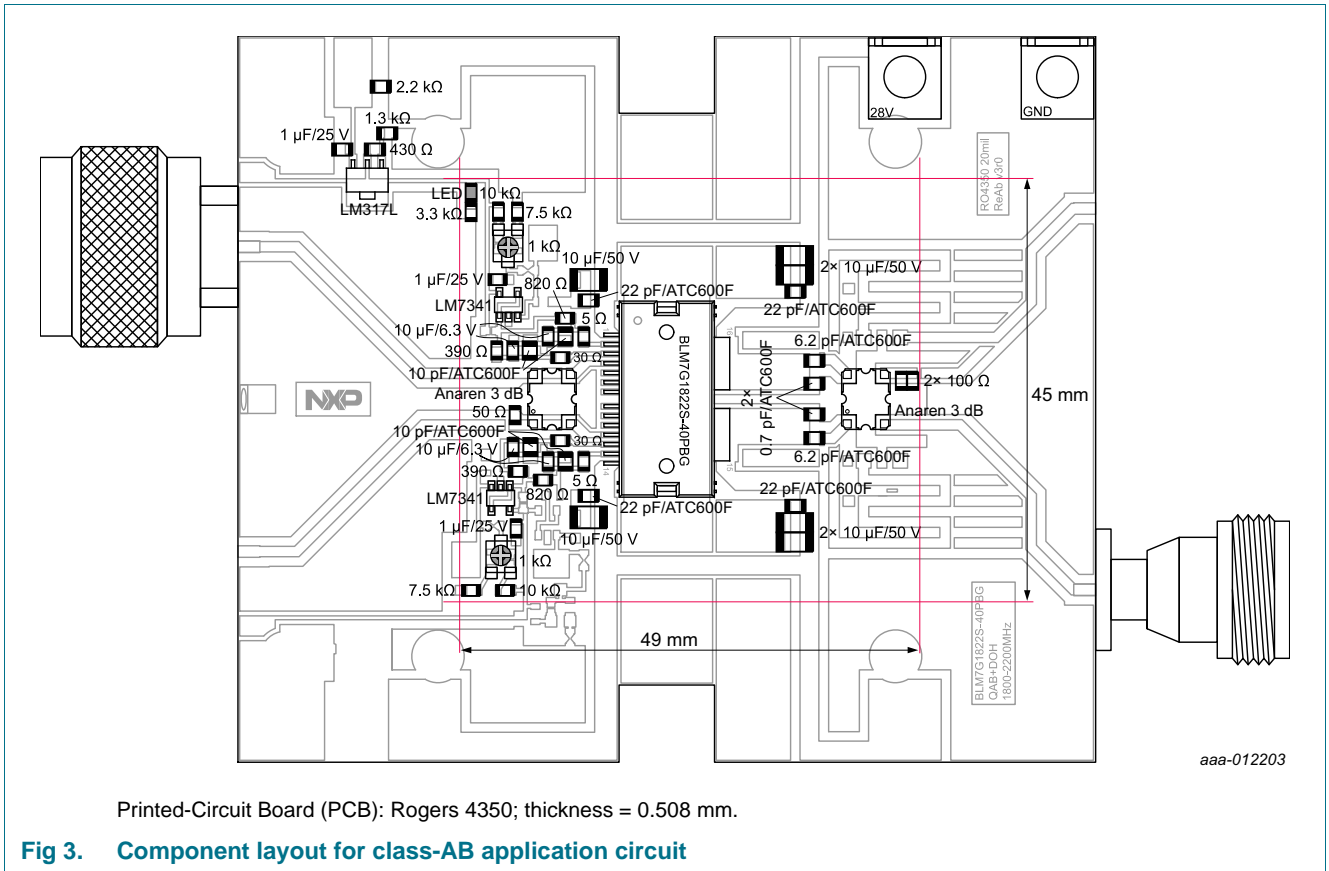
[2]  $f = 2170\text{ MHz}$ .

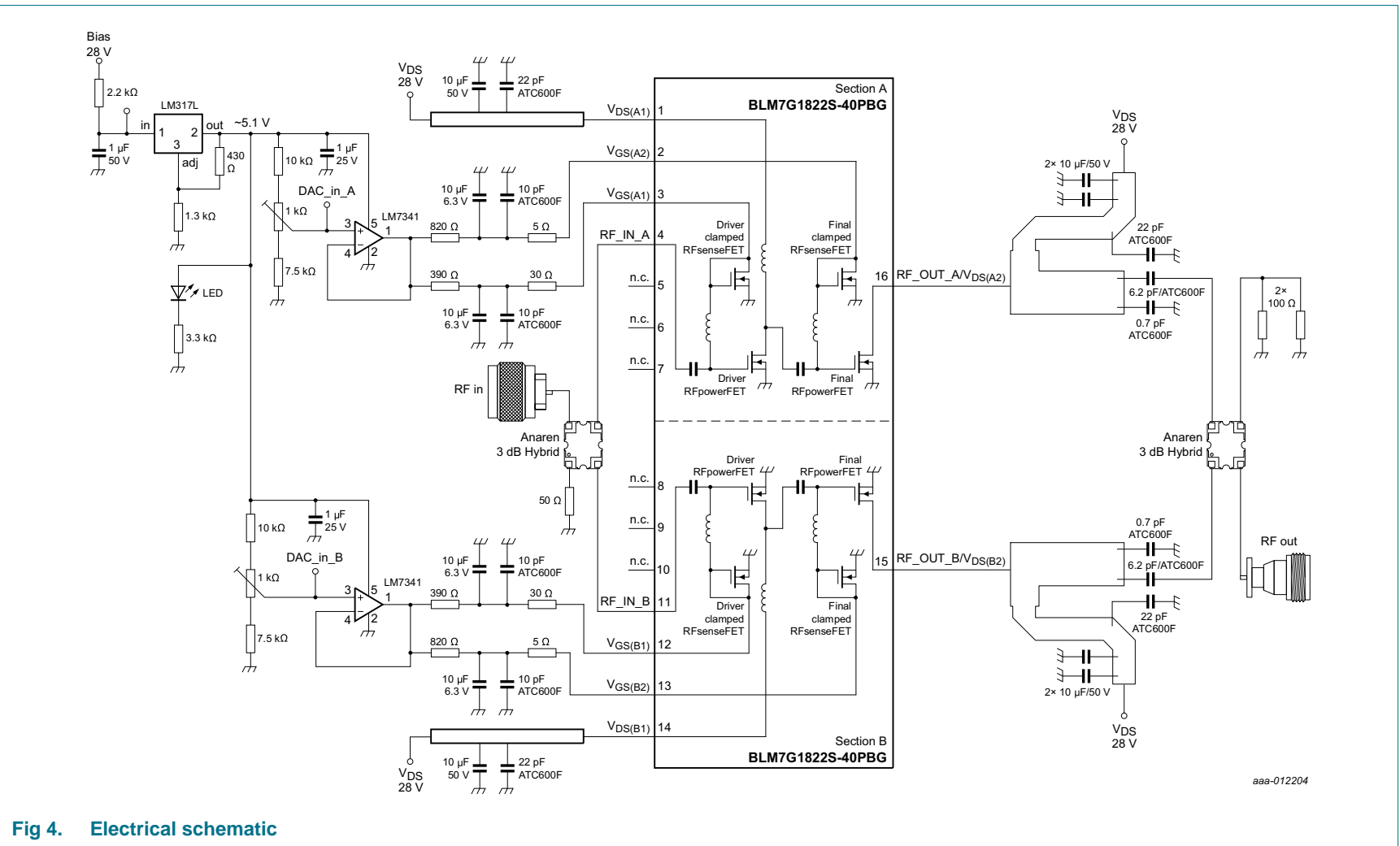
## 8. Application information

**Table 8. Typical performance**

Test signal: 1-tone CW; RF performance at  $T_{case} = 25\text{ °C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 80\text{ mA}$  (both sections);  $I_{Dq2} = 240\text{ mA}$  (both sections) unless otherwise specified, measured in a NXP wideband  $f = 1805\text{ MHz}$  to  $2170\text{ MHz}$  class AB application circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(1dB)}$	output power at 1 dB gain compression	$f = 1960\text{ MHz}$	-	45.1	-	W
$\eta_D$	drain efficiency	at $P_{L(1dB)}$ ; $f = 1960\text{ MHz}$	-	53.3	-	%
$G_p$	power gain	$P_{L(AV)} = 4\text{ W}$ ; $f = 1960\text{ MHz}$	-	31.6	-	dB
$B_{video}$	video bandwidth	2-tone CW; $P_{L(AV)} = 4\text{ W}$ ; $f = 1960\text{ MHz}$	-	140	-	MHz
$G_{flat}$	gain flatness	$P_{L(AV)} = 4\text{ W}$	-	0.2	-	dB
$\Delta G/\Delta T$	gain variation with temperature	$f = 1960\text{ MHz}$	-	0.03	-	dB/°C
$ S_{12} ^2$	isolation	between sections A and B; $P_{L(AV)} = 4\text{ W}$ ; $f = 1960\text{ MHz}$	-	27.8	-	dB
K	Rollett stability factor	$T = -40\text{ °C}$ ; $f = 0.1\text{ GHz}$ to $3\text{ GHz}$	-	>1	-	





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Fig 4. Electrical schematic

## 8.1 Possible circuit topologies

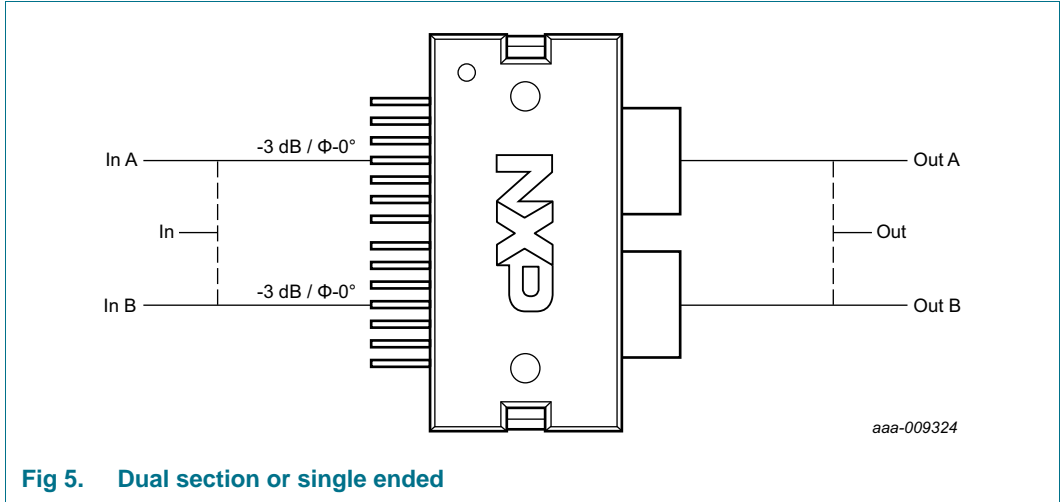


Fig 5. Dual section or single ended

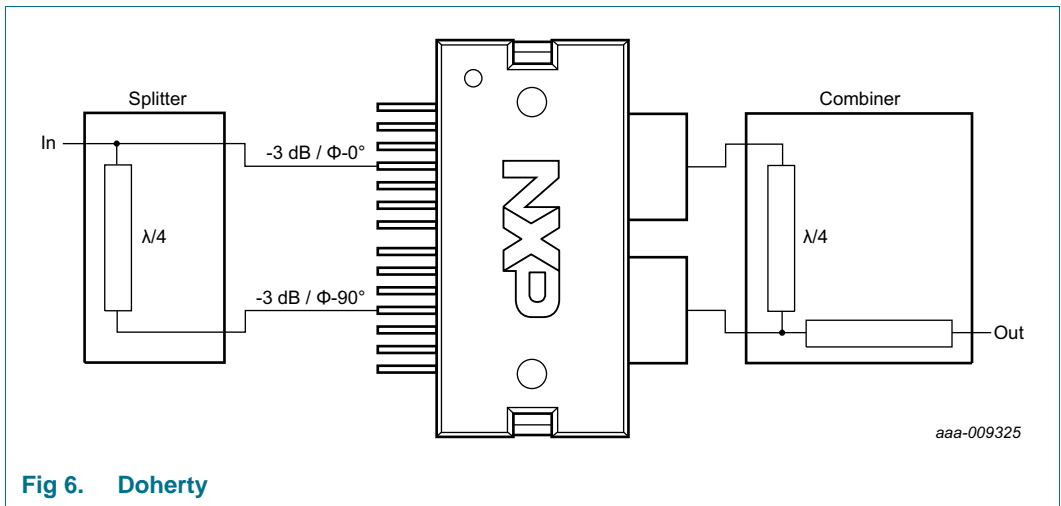


Fig 6. Doherty

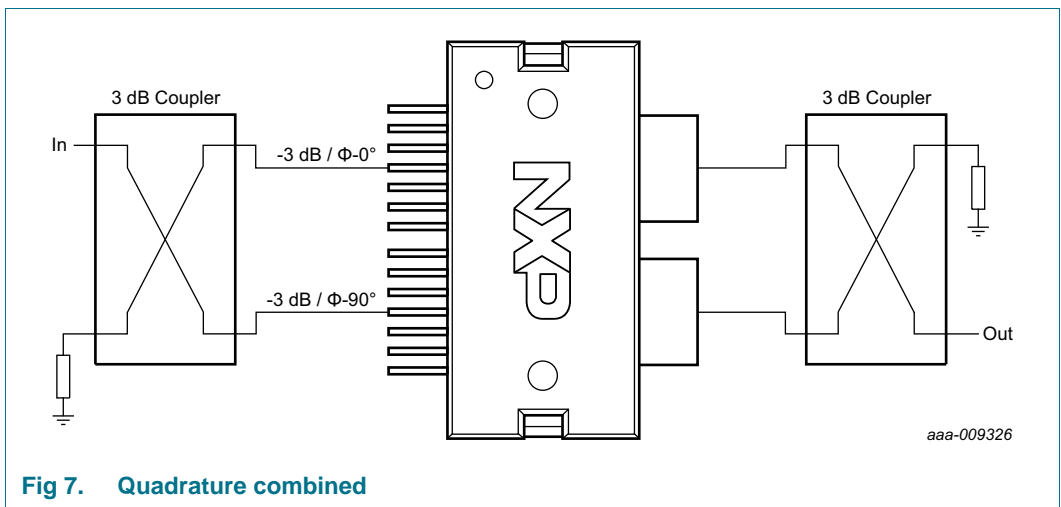
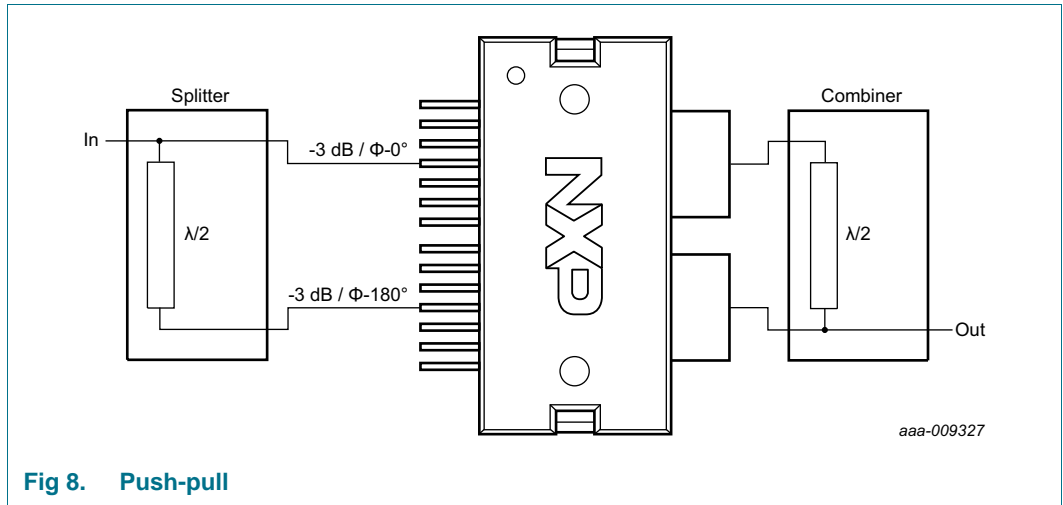


Fig 7. Quadrature combined





**8.2 Ruggedness in class-AB operation**

The BLM7G1822S-40PB and BLM7G1822S-40PBG are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 80\text{ mA}$ ;  $I_{Dq2} = 240\text{ mA}$ ;  $P_1 = 16\text{ dBm (CW)}$ ;  $f = 2140\text{ MHz}$ .

**8.3 Impedance information**

**Table 9. Typical impedance tuned for maximum output power**

Measured load-pull data per section; test signal: pulsed CW;  $T_{case} = 25\text{ °C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 110\text{ mA}$ ;  $t_p = 100\text{ }\mu\text{s}$ ;  $\delta = 10\text{ %}$ ;  $Z_S = 50\text{ }\Omega$ . Typical values unless otherwise specified.

f	at 1dB gain compression point					at 3dB gain compression point				
	Z <sub>L</sub>	G <sub>p(max)</sub>	P <sub>L</sub>	$\eta_{add}$	AM-PM conversion	Z <sub>L</sub>	G <sub>p(max)</sub>	P <sub>L</sub>	$\eta_{add}$	AM-PM conversion
(MHz)	( $\Omega$ )	(dB)	(W)	(%)	(deg)	( $\Omega$ )	(dB)	(W)	(%)	(deg)
<b>BLM7G1822S-40PB</b>										
1805	7.2 – j9.2	32.2	45	48.3	1.7	7.7 – j10.6	32.2	45.8	51	0.3
1842.5	7.2 – j9.2	32.3	45	49	2.3	7.8 – j10.6	32.3	45.8	51.8	0.9
1880	7.2 – j9.2	32.4	44.9	49.9	2.7	7.7 – j10.6	32.3	45.8	52.1	1.4
1930	7.3 – j9.2	32.5	44.9	50.5	1.8	6.7 – j10.8	32	45.7	48.8	0.3
1960	7.2 – j9.2	32.7	45	50.8	3.3	7.8 – j10.6	32.6	45.7	51.4	1.6
1990	7.2 – j9.2	32.8	45	51	3.3	6.3 – j9.5	32.5	45.7	49.1	0.5
2110	6.3 – j9.5	33	45.2	50.7	2.2	6.3 – j9.5	33	45.8	51.4	-4
2140	6.3 – j9.5	33	45.1	50.7	1.2	6.3 – j9.5	33	45.7	51.8	-5.9
2170	6.3 – j9.5	33	45.1	51.3	0.3	6.8 – j10.8	32.8	45.6	50.1	-7.5
<b>BLM7G1822S-40PBG</b>										
1805	8.7 – j11.9	32.1	45	50.8	-0.2	8.0 – j13.4	31.8	45.8	50.3	-1.7
1842.5	8.7 – j11.8	32.3	45	50.6	0.4	8.0 – j13.4	31.9	45.8	49.2	-1
1880	7.5 – j12.0	32.1	45	48.6	1.4	8.0 – j13.4	32.1	45.8	50	-0.3
1930	8.0 – j13.4	32.1	45	48.7	1.6	8.0 – j13.4	32.1	45.8	50.3	-0.6
1960	7.5 – j12.1	32.5	45	49.5	1.7	8.0 – j13.4	32.4	45.7	49.9	-0.4

**Table 9. Typical impedance tuned for maximum output power ...continued**

Measured load-pull data per section; test signal: pulsed CW;  $T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 110\text{ mA}$ ;  $t_p = 100\text{ }\mu\text{s}$ ;  $\delta = 10\text{ }\%$ ;  $Z_S = 50\text{ }\Omega$ . Typical values unless otherwise specified.

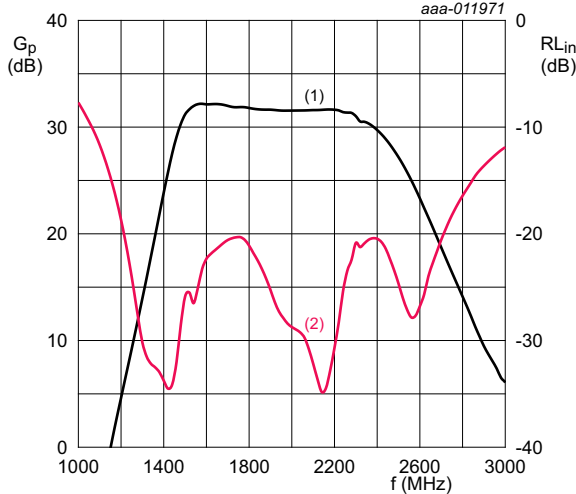
f	at 1dB gain compression point					at 3dB gain compression point				
	Z <sub>L</sub>	G <sub>p(max)</sub>	P <sub>L</sub>	$\eta_{add}$	AM-PM conversion	Z <sub>L</sub>	G <sub>p(max)</sub>	P <sub>L</sub>	$\eta_{add}$	AM-PM conversion
(MHz)	( $\Omega$ )	(dB)	(W)	(%)	(deg)	( $\Omega$ )	(dB)	(W)	(%)	(deg)
1990	8.0 – j13.3	32.6	45	49	2.4	7.7 – j15.2	32.2	45.7	47	-0.7
2110	8.1 – j13.4	33	45.2	51	0.8	8.1 – j13.4	33	45.8	52.1	-6.1
2140	6.5 – j12.8	32.7	45.1	49.9	-0.8	6.5 – j12.8	32.7	45.7	50.8	-8.9
2170	7.0 – j14.1	32.4	45.1	48.3	-1.5	7.0 – j14.1	32.4	45.6	49.1	-10

**Table 10. Typical impedance tuned for maximum power added efficiency**

Measured load-pull data per section; test signal: pulsed CW;  $T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 110\text{ mA}$ ;  $t_p = 100\text{ }\mu\text{s}$ ;  $\delta = 10\text{ }\%$ ;  $Z_S = 50\text{ }\Omega$ . Typical values unless otherwise specified.

f	at 1dB gain compression point					at 3dB gain compression point				
	Z <sub>L</sub>	G <sub>p(max)</sub>	P <sub>L</sub>	$\eta_{add}$	AM-PM conversion	Z <sub>L</sub>	G <sub>p(max)</sub>	P <sub>L</sub>	$\eta_{add}$	AM-PM conversion
(MHz)	( $\Omega$ )	(dB)	(W)	(%)	(deg)	( $\Omega$ )	(dB)	(W)	(%)	(deg)
<b>BLM7G1822S-40PB</b>										
1805	18.0 – j7.9	33.4	43.1	57.8	-0.6	16.7 – j4.2	33.5	43.9	58.8	-4.9
1842.5	16.6 – j4.0	33.5	43	58	-1.1	16.2 – j5.6	33.4	44	58.5	-3
1880	14.2 – j5.6	33.4	43.6	57.9	0.4	12.2 – j4.6	33.4	44.5	58.4	-2.8
1930	11.6 – j3.4	33.5	43.4	57.5	-1.6	11.6 – j3.4	33.5	44.1	57.7	-4.3
1960	9.9 – j4.4	33.6	43.9	57.5	0.3	9.9 – j4.4	33.6	44.6	57.6	-2.3
1990	10.8 – j3.1	33.7	43.4	57.4	0.2	8.6 – j4.3	33.6	44.6	57	-3.1
2110	7.3 – j4.8	33.8	43.9	57.5	-0.2	7.3 – j4.8	33.8	44.6	56.4	-4.4
2140	7.3 – j4.8	33.8	43.9	57.5	-0.5	7.3 – j4.8	33.8	44.5	56.2	-5.4
2170	7.0 – j6.3	33.6	44.3	57.2	-0.3	7.0 – j6.3	33.6	44.9	56.5	-7
<b>BLM7G1822S-40PBG</b>										
1805	18.8 – j9.7	33	43.2	57.4	-2.4	14.8 – j8.7	33	44.6	58.1	-5.5
1842.5	16.9 – j6.3	33.2	43.2	57.4	-2.7	16.3 – j4.3	33.3	44.7	57.5	-7.4
1880	15.3 – j5.5	33.3	43.2	57.2	-1.9	12.7 – j7.1	33.2	44.5	57.3	-4.3
1930	12.8 – j7.3	33.2	43.7	56.7	-0.9	12.8 – j7.3	33.2	44.4	56.3	-3.4
1960	11.1 – j6.8	33.5	43.8	56.5	-1	11.1 – j6.8	33.5	44.5	56.1	-3.6
1990	9.6 – j6.5	33.5	43.7	56.3	-0.9	9.0 – j7.7	33.4	44.8	55.9	-3.4
2110	9.0 – j7.7	33.7	44	57.1	-0.4	7.6 – j8.0	33.6	44.7	56.1	-6.7
2140	8.1 – j6.7	33.6	43.5	56.9	-1.6	7.6 – j8.0	33.5	44.5	55.7	-7.7
2170	6.4 – j7.7	33.3	43.6	57.2	-3	8.6 – j9.0	33.3	44.8	55.8	-7.8

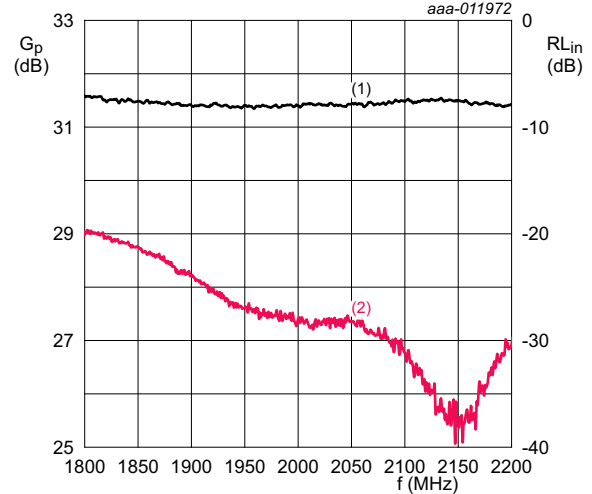
**8.4 Graphs**



$T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 120\text{ mA}$ ;  $P_L = 4\text{ W}$ . Per section.

- (1) magnitude of  $G_p$
- (2) magnitude of  $RL_{in}$

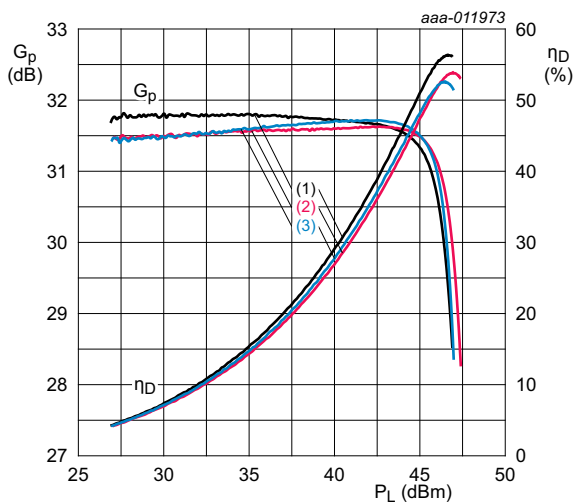
**Fig 9. Wideband power gain and input return loss as function of frequency; typical values**



$T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 120\text{ mA}$ ;  $P_L = 4\text{ W}$ . Per section.

- (1) magnitude of  $G_p$
- (2) magnitude of  $RL_{in}$

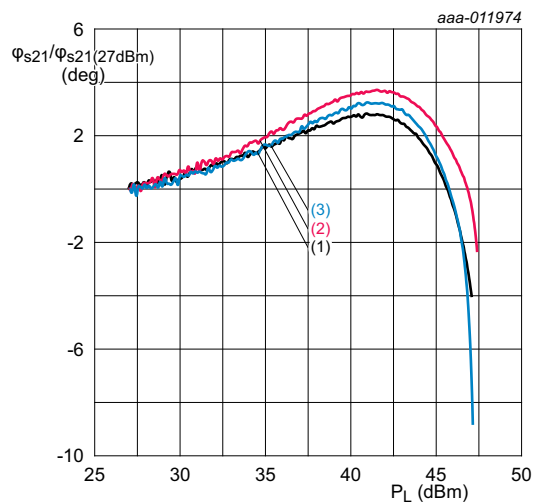
**Fig 10. In-band power gain and input return loss as function of frequency; typical values**



$T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 120\text{ mA}$ . Per section.

- (1)  $f = 1805\text{ MHz}$
- (2)  $f = 1960\text{ MHz}$
- (3)  $f = 2170\text{ MHz}$

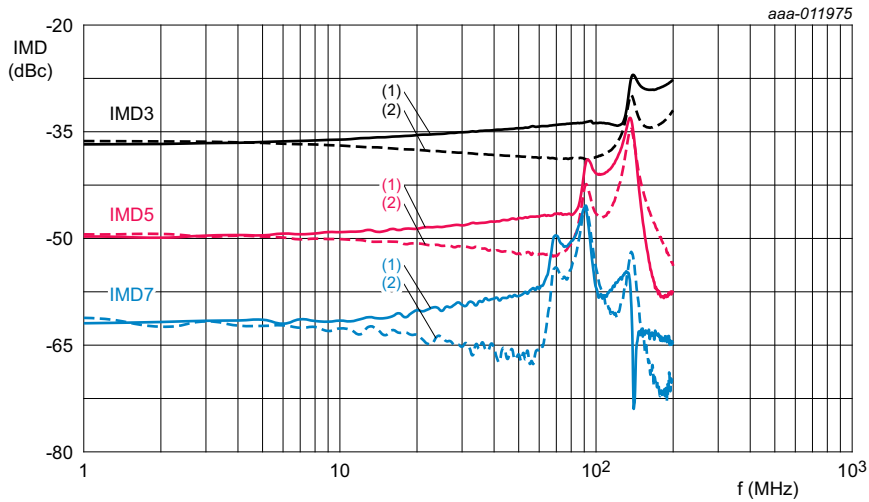
**Fig 11. Power gain and drain efficiency as function of output power; typical values**



$T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 120\text{ mA}$ . Per section.

- (1)  $f = 1805\text{ MHz}$
- (2)  $f = 1960\text{ MHz}$
- (3)  $f = 2170\text{ MHz}$

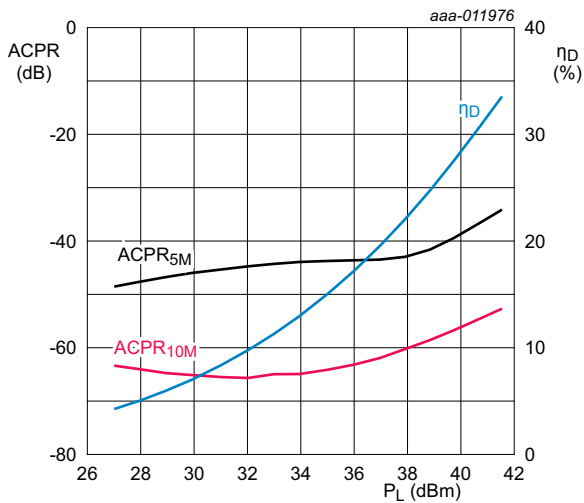
**Fig 12. 27 dBm normalized phase response as a function of output power; typical values**



$T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 120\text{ mA}$ ;  $f = 1960\text{ MHz}$ ; 2-tone CW;  $P_{L(AV)} = 4\text{ W}$ . Per section.

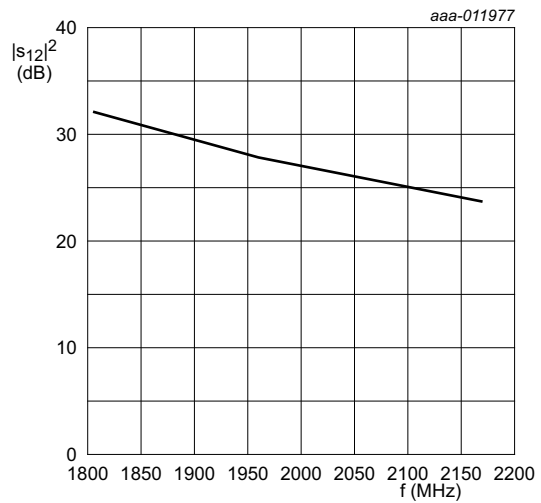
- (1) IMD low
- (2) IMD high

Fig 13. Intermodulation distortion as a function of tone spacing; typical values



$T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 120\text{ mA}$ ;  $f = 1960\text{ MHz}$ ; 1-carrier W-CDMA; test model 1;  $PAR = 7.2\text{ dB}$  at 0.01 % probability on CCDF. Per section.

Fig 14. Adjacent channel power ratio and drain efficiency as function of output power; typical values



$T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $V_{DS} = 28\text{ V}$ ;  $I_{Dq1} = 40\text{ mA}$ ;  $I_{Dq2} = 120\text{ mA}$ . Per section.

Fig 15. Isolation as a function of frequency; typical values

9. Package outline

HSOP16F: plastic, heatsink small outline package; 16 leads(flat)

SOT1211-1

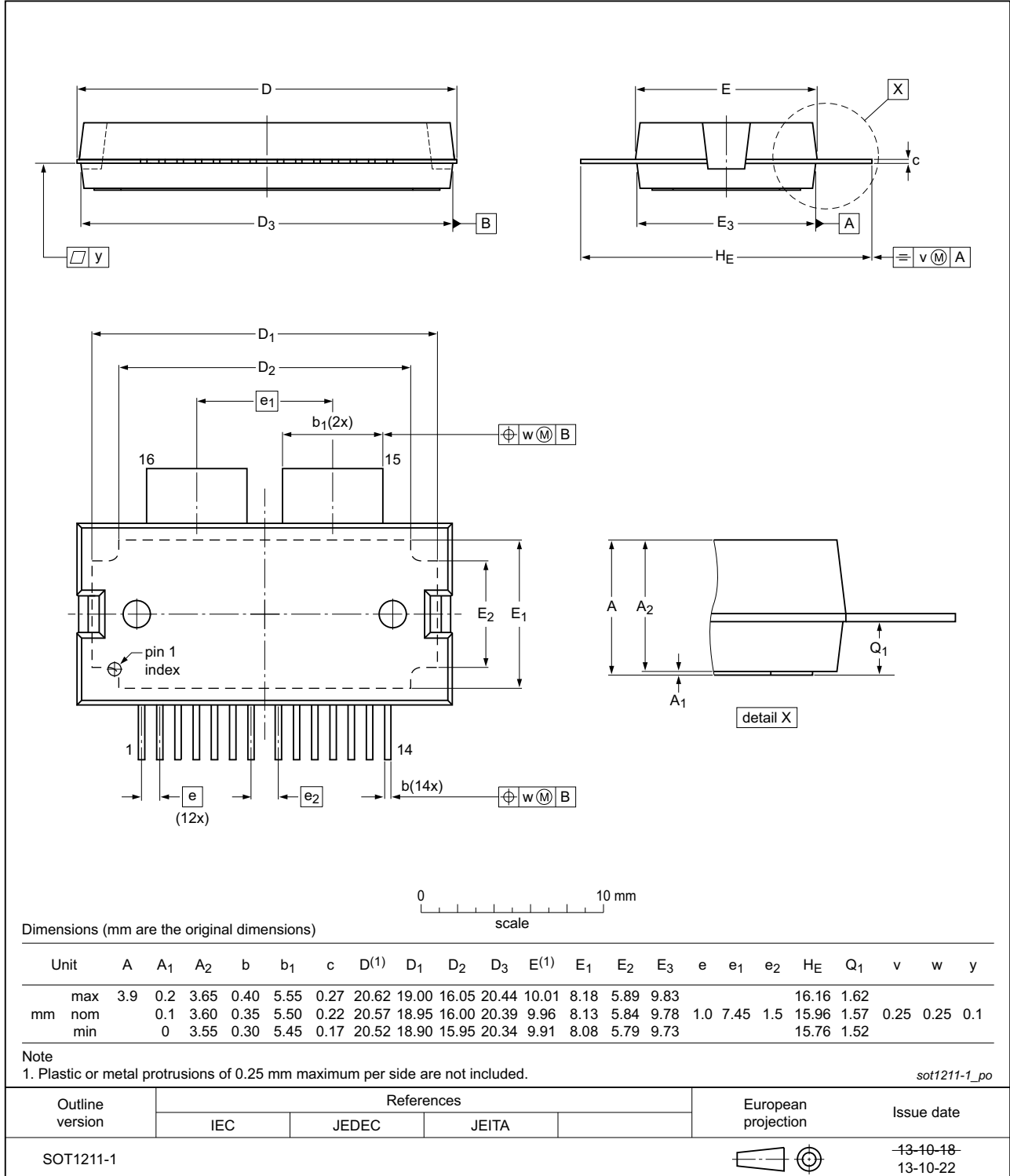


Fig 16. Package outline SOT1211-1 (HSOP16F)

HSOP16: plastic, heatsink small outline package; 16 leads

SOT1212-1

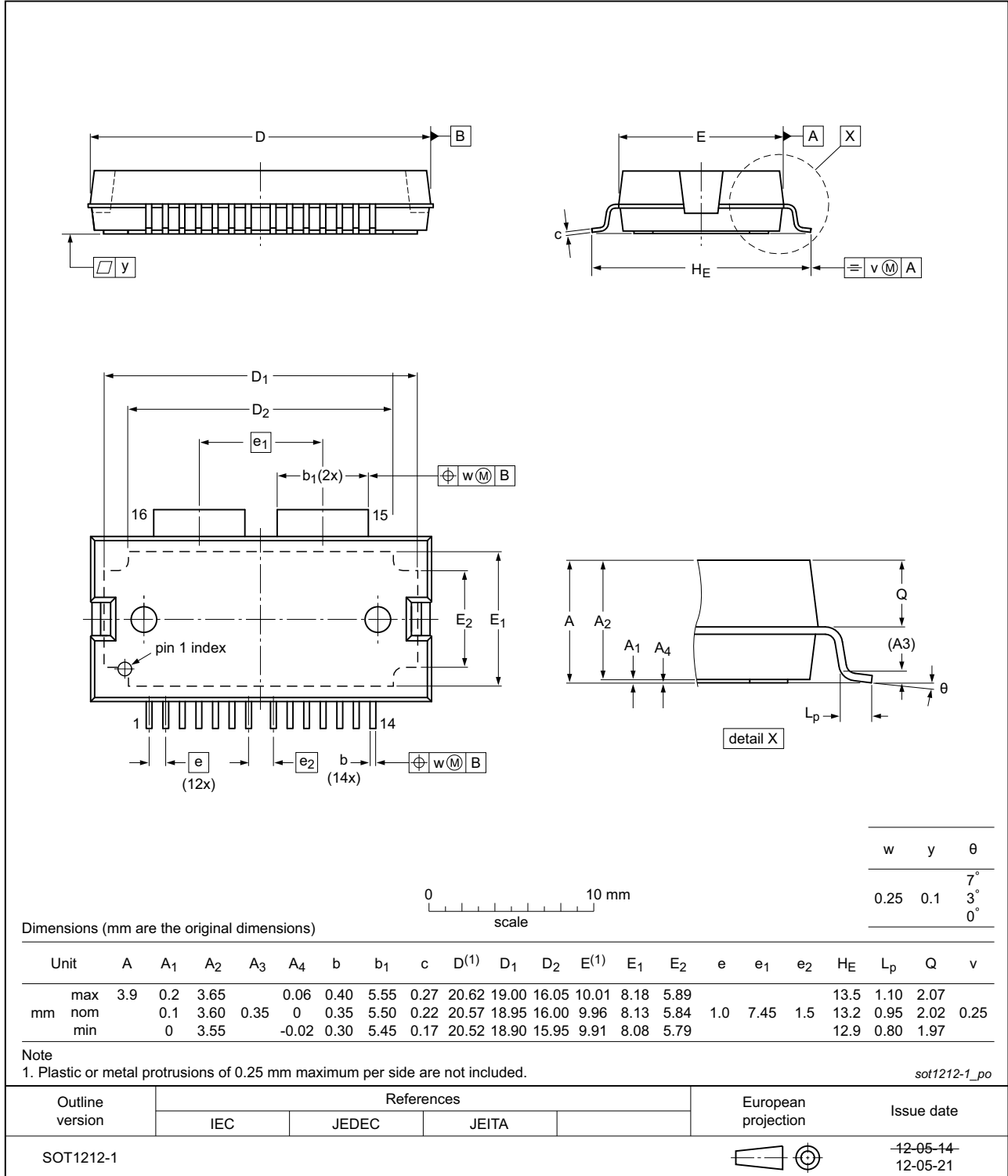


Fig 17. Package outline SOT1212-1 (HSOP16)

## 10. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

## 11. Abbreviations

Table 11. Abbreviations

Acronym	Description
AM	Amplitude Modulation
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
GEN7	Seventh Generation
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MMIC	Monolithic Microwave Integrated Circuit
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
PM	Phase Modulation
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

## 12. Revision history

**Table 12. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLM7G1822S-40PB_S-40PBG v.2	20140324	Product data sheet	-	BLM7G1822S-40PB_S-40PBG v.1
Modifications:	<ul style="list-style-type: none"> <li>• <a href="#">Table 1 on page 1</a>: several updates have been made</li> <li>• <a href="#">Section 1.2 on page 1</a>: the term “path” has been replaced with “section:”</li> <li>• <a href="#">Table 2 on page 2</a>: the term “path” has been replaced with “section:”</li> <li>• <a href="#">Table 4 on page 3</a>: the table note has been updated</li> <li>• <a href="#">Table 5 on page 4</a>: several updates have been made</li> <li>• <a href="#">Table 6 on page 4</a>: several updates have been made</li> <li>• <a href="#">Table 7 on page 5</a>: several updates have been made</li> <li>• <a href="#">Figure 3 on page 6</a>: the figure has been added</li> <li>• <a href="#">Figure 4 on page 7</a>: the figure has been added</li> <li>• <a href="#">Section 8.2 on page 9</a>: the section has been added</li> <li>• <a href="#">Section 8.3 on page 9</a>: the section has been added</li> <li>• <a href="#">Section 8.4 on page 11</a>: the section has been added</li> <li>• <a href="#">Table 11 on page 15</a>: several updates have been made</li> </ul>			
BLM7G1822S-40PB_S-40PBG v.1	20131009	Objective data sheet	-	-



## 13. Legal information

### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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